

ABSTRACT OF THE INVENTION

A first insulating hydrogen barrier film is filled between lower electrodes of some ferroelectric capacitors arranged along one direction out of a word line direction and a bit line direction among a plurality of ferroelectric capacitors included in a ferroelectric memory of this invention. A common capacitor dielectric film commonly used by the some ferroelectric capacitors arranged along the one direction is formed on the lower electrodes of the some ferroelectric capacitors arranged along the one direction and on the first insulating hydrogen barrier film. A common upper electrode commonly used by the some ferroelectric capacitors arranged along the one direction is formed on the common capacitor dielectric film. A second insulating hydrogen barrier film is formed so as to cover the common upper electrode.